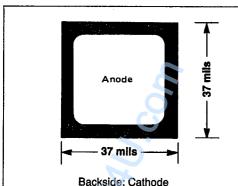
DIE NO. **IC5819** LINE SOURCE — DRL754



Designed for Schottky Barrier low-voltage high-frequency rectifier applications. This die provides performance equal to or better than that of the following device types:

> 1N5817 1N5818 1N5819



METALLIZATION Top* Cr Ni Au Back Cr Ni Au
DIE THICKNESS 7 ± 2
BONDING PAD SIZE: Anode
*BONDING — Rectifier chips are designed for solder connections on both sides. Conductive epoxy could be substituted. The metallization is wire bondable using thermocompression or ultrasonic techniques, but adjustments in the machine settings may be necessary because of the metallization system.

ELECTRICAL CHARACTERISTICS (T_A = 25°C; Note 1)

Parameter	Test Conditions	Min	Max	Unit
V _{RRM} /V _R		40	_	Volts
V _F	I _F = 1.0 Amp		0.60	Volts
I _R	V _R = 40 Volts		1.0	mAdc

NOTES:

- Because of the limitations of probe testing, only dc parameters are tested. These parameters must be measured using pulse techniques: pulse width ≤ 300 μs, duty cycle ≤ 2%.
- 2. Detailed device characteristics are available from your Motorola sales representative.